Central™
Semiconductor Corp.

PROCESS CPD48V

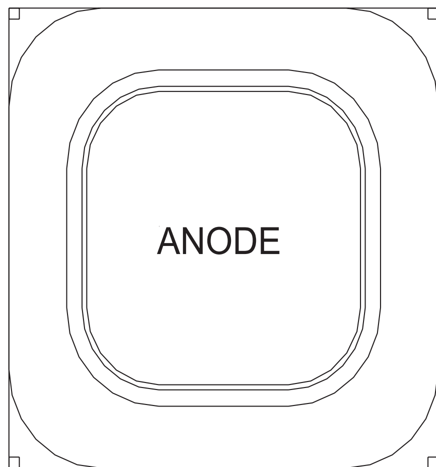
Schottky Diode

High Current Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	14 x 14 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	9.0 x 9.0 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

59,940

PRINCIPAL DEVICE TYPES

CMPSH-3 Series
CMSSH-3 Series
CMXSH-3
CMKSH-3T

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
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www.centralsemi.com

R2 (8-October 2008)

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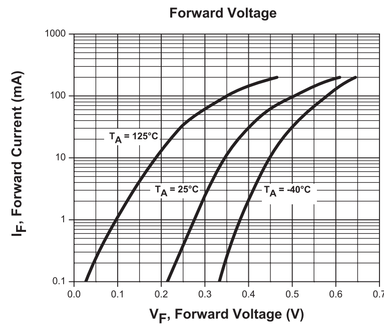
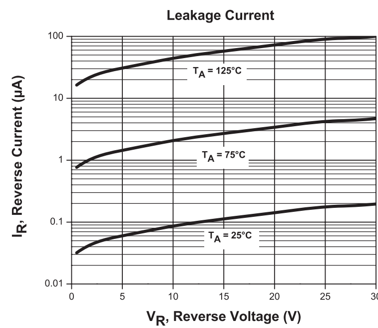
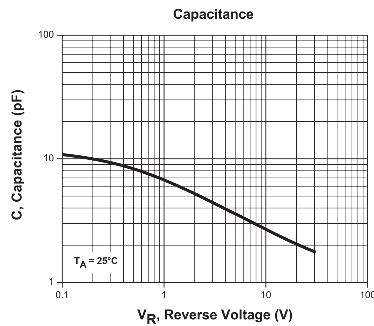
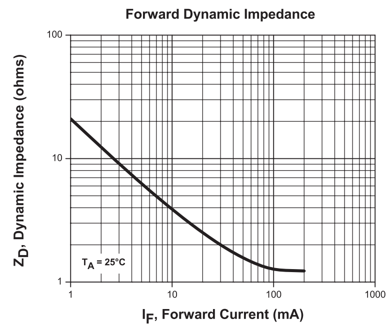
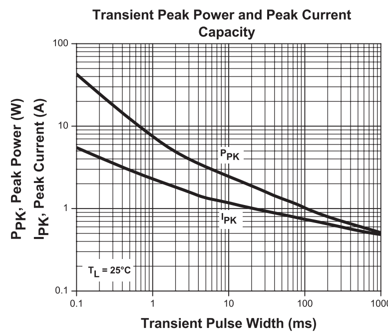
PROCESS CPD48V
Typical Electrical Characteristics

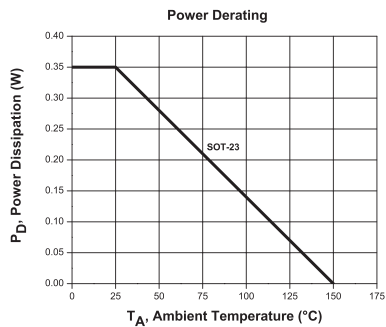












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